

PMBFJ111; PMBFJ112; PMBFJ113

N-channel junction FETs

Rev. 03 — 4 August 2004

Product data sheet

1. Product profile

1.1 General description

Symmetrical N-channel junction FETs in a SOT23 package.

1.2 Features

- High-speed switching
- Interchangeability of drain and source connections
- Low R_{DSon} at zero gate voltage (< 30 Ω for PMBFJ111).

1.3 Applications

- Analog switches
- Choppers
- Commutators
- Multiplexers
- Thin and thick film hybrids.

2. Pinning information

Table 1: Pinning

Pin	Description [1]	Simplified outline	Symbol
1	drain		
2	source]3	
3	gate	1 2	3 1 2 sym053

[1] Drain and source are interchangeable.



3. Ordering information

Table 2: Ordering information

Type number	Package	Package				
	Name	Description	Version			
PMBFJ111	-	plastic surface mounted package; 3 leads	SOT23			
PMBFJ112	_					
PMBFJ113						

4. Marking

Table 3: Marking

<u> </u>	
Type number	Marking code [1]
PMBFJ111	41*
PMBFJ112	42*
PMBFJ113	47*

^{[1] * =} p: Made in Hong Kong

5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±40	V
V _{GSO}	gate-source voltage		-	-40	V
V_{GDO}	gate-drain voltage		-	-40	V
I _G	forward gate current (DC)		-	50	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[1]</u> _	300	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

^[1] Mounted on a ceramic substrate, 8 mm \times 10 mm \times 0.7 mm.

6. Thermal characteristics

Table 5: Thermal characteristics

 $T_j = P (R_{th(j-t)} + R_{th(t-s)} + R_{th(s-a)}) + T_{amb}.$

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1] 430	K/W
	thermal resistance from junction to ambient		² 500	K/W

^[1] Mounted on a ceramic substrate, 8 mm \times 10 mm \times 0.7 mm.

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^{* =} t: Made in Malaysia

^{* =} W: Made in China

^[2] Mounted on printed circuit board.

7. Static characteristics

Table 6: Static characteristics

 $T_i = 25 \,^{\circ}C$.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{GSS}	gate-source leakage current	$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	-1	nΑ
I _{DSS}	drain-source leakage current					
	PMBFJ111	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	20	-	-	mΑ
	PMBFJ112	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	5	-	-	mΑ
	PMBFJ113	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	2	-	-	mΑ
V _{(BR)GSS}	gate-source breakdown voltage	$I_G = -1 \mu A; V_{DS} = 0 V$	-40	-	-	V
V_{GSoff}	gate-source cut-off voltage					
	PMBFJ111	$I_D = 1 \mu A; V_{DS} = 5 V$	-10	-	-3	V
	PMBFJ112	$I_D = 1 \mu A; V_{DS} = 5 V$	-5	-	-1	V
	PMBFJ113	$I_D = 1 \mu A; V_{DS} = 5 V$	-3	-	-0.5	V
R _{DSon}	drain-source on-state resistance					
	PMBFJ111	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	30	Ω
	PMBFJ112	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	50	Ω
	PMBFJ113	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	100	Ω

8. Dynamic characteristics

Table 7: Dynamic characteristics

Symbol	Parameter	Conditions	Mir	т Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; f = 1 \text{ MHz}$	-	6	-	pF
		$V_{DS} = 0 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	22	28	pF
C _{rss}	feedback capacitance		-	3	-	pF
Switching	g times; see Figure 2					
t _r	rise time		<u>[1]</u> _	6	-	ns
t _{on}	turn-on time		<u>[1]</u> _	13	-	ns
t _f	fall time		<u>[1]</u> _	15	-	ns
t _{off}	turn-off time		<u>[1]</u> -	35	-	ns

[1] Test conditions for switching times are as follows:

 V_{DD} = 10 V, V_{GS} = 0 V to V_{GSoff} (all types);

 V_{GSoff} = -12 V, R_L = 750 Ω (PMBFJ111);

 $V_{GSoff} = -7 \text{ V}, R_L = 1550 \Omega \text{ (PMBFJ112)};$

 V_{GSoff} = -5 V, R_L = 3150 Ω (PMBFJ113).

Product data sheet

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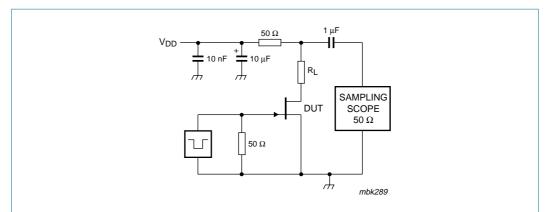


Fig 1. Switching circuit.

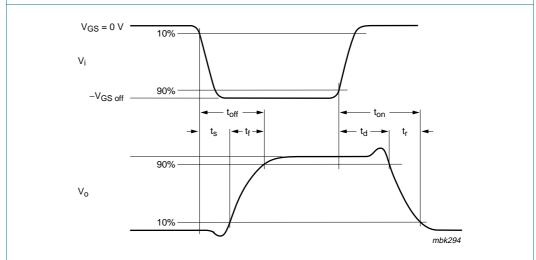


Fig 2. Input and output waveforms.

9. Package outline

Plastic surface mounted package; 3 leads

SOT23

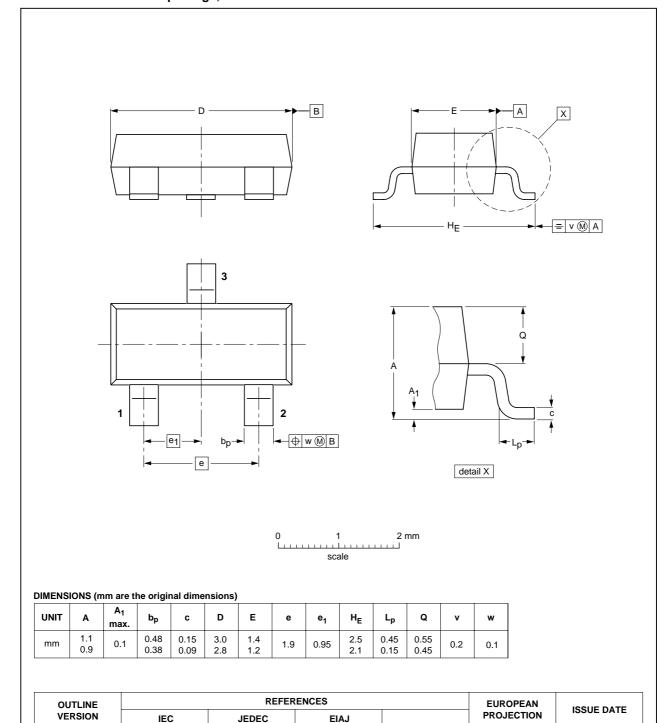


Fig 3. Package outline.

SOT23

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97-02-28

99-09-13

TO-236AB

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Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMBFJ111_112_113_ 3	20040804	Product data sheet	-	9397 750 13402	PMBFJ111_112_113_ CNV_2
Modifications:	 The format of this data sheet I information standard of Philips 			to comply with the	new presentation and
	Table 3 "M	<mark>larking"</mark> : added new m	arking codes		
PMBFJ111_112_113_ CNV_2	19971201	Product specification	-	not applicable	-

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Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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